56855

Data Sheet Technical Data

56800E 16-bit Digital Signal Controllers

DSP56855 Rev. 6 01/2007

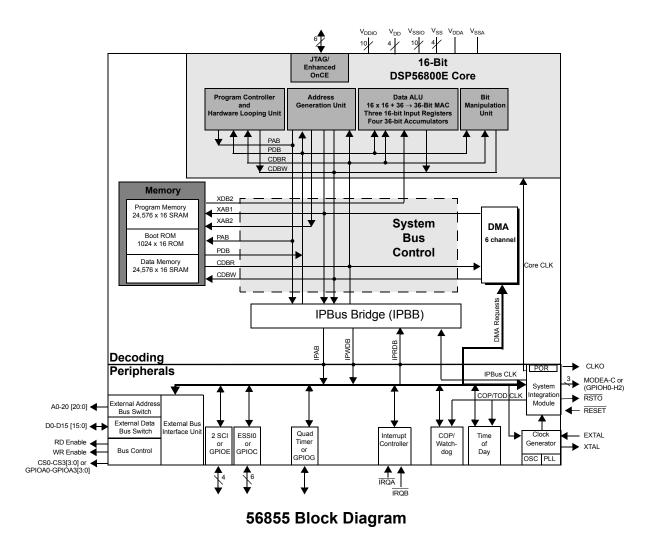


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56855 General Description

- 120 MIPS at 120MHz
- 24K x 16-bit Program SRAM
- 24K x 16-bit Data SRAM
- 1K x 16-bit Boot ROM
- Access up to 2M words of program memory or 8M words of data memory
- Chip Select Logic for glueless interface to ROM and SRAM
- Six (6) independent channels of DMA
- Enhanced Synchronous Serial Interface (ESSI)

- Two (2) Serial Communication Interfaces (SCI)
- General Purpose 16-bit Quad Timer with 1 external pin
- JTAG/Enhanced On-Chip Emulation (OnCE™) for unobtrusive, real-time debugging
- Computer Operating Properly (COP)/Watchdog Timer
- Time-of-Day (TOD)
- 100 LQFP package
- Up to 18 GPIO



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Part 1 Overview

1.1 56855 Features

1.1.1 Core

- Efficient 16-bit engine with dual Harvard architecture
- 120 Million Instructions Per Second (MIPS) at 120MHz core frequency
- Single-cycle 16 × 16-bit parallel Multiplier-Accumulator (MAC)
- Four (4) 36-bit accumulators including extension bits
- 16-bit bidirectional shifter
- Parallel instruction set with unique DSP addressing modes
- Hardware DO and REP loops
- Three (3) internal address buses and one (1) external address bus
- Four (4) internal data buses and one (1) external data bus
- Instruction set supports both DSP and controller functions
- Four (4) hardware interrupt levels
- Five (5) software interrupt levels
- Controller-style addressing modes and instructions for compact code
- Efficient C Compiler and local variable support
- Software subroutine and interrupt stack with depth limited only by memory
- JTAG/Enhanced OnCE debug programming interface

1.1.2 Memory

- Harvard architecture permits up to three (3) simultaneous accesses to program and data memory
- On-Chip Memory
 - 24K × 16-bit Program SRAM
 - 24K × 16-bit Data SRAM
 - 1K × 16-bit Boot ROM
- Off-Chip Memory Expansion (EMI)
 - Access up to 2M words of program memory or 8M words of data memory
 - Chip Select Logic for glue-less interface to ROM and SRAM

1.1.3 Peripheral Circuits for 56855

- General Purpose 16-bit Quad Timer with 1 external pin*
- Two (2) Serial Communication Interfaces (SCI)*
- Enhanced Synchronous Serial Interface (ESSI) module*
- Computer Operating Properly (COP)/Watchdog Timer
- JTAG/Enhanced On-Chip Emulation (EOnCE) for unobtrusive, real-time debugging

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- Six (6) independent channels of DMA
- Time-of-Day (TOD)
- Up to 18 GPIO

* Each peripheral I/O can be used alternately as a General Purpose I/O if not needed

1.1.4 Energy Information

- Fabricated in high-density CMOS with 3.3V, TTL-compatible digital inputs
- Wait and Stop modes available

1.2 56855 Description

The 56855 is a member of the 56800E core-based family of controllers. It combines, on a single chip, the processing power of a Digital Signal Processor (DSP) and the functionality of a microcontroller with a flexible set of peripherals, creating an extremely cost-effective solution. Because of its low cost, configuration flexibility, and compact program code, the 56855 is well-suited for many applications. The 56855 includes many peripherals that are especially useful for low-end Internet appliance applications and low-end client applications such as telephony; portable devices; Internet audio; and point-of-sale systems, such as noise suppression; ID tag readers; sonic/subsonic detectors; security access devices; remote metering; sonic alarms.

The 56800E core is based on a Harvard-style architecture consisting of three execution units operating in parallel, allowing as many as six operations per instruction cycle. The microprocessor-style programming model and optimized instruction set allow straightforward generation of efficient, compact code for both DSP and MCU applications. The instruction set is also highly efficient for C Compilers, enabling rapid development of optimized control applications.

The 56855 supports program execution from either internal or external memories. Two data operands can be accessed from the on-chip Data RAM per instruction cycle. The 56855 also provides two external dedicated interrupt lines, and up to 18 General Purpose Input/Output (GPIO) lines, depending on peripheral configuration.

The 56855 controller includes 24K words of Program RAM, 24K words of Data RAM and 1K of Boot ROM. It also supports program execution from external memory.

This controller also provides a full set of standard programmable peripherals that include one Enhanced Synchronous Serial Interface (ESSI), two Serial Communications Interfaces (SCI), and one Quad Timer. The ESSI, SCIs, four chip selects and Quad Timer external output can be used as General Purpose Input/Outputs when its primary function is not required.

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1.3 State of the Art Development Environment

- Processor ExpertTM (PE) provides a Rapid Application Design (RAD) tool that combines easy-to-use component-based software application creation with an expert knowledge system.
- The Code Warrior Integrated Development Environment is a sophisticated tool for code navigation, compiling, and debugging. A complete set of evaluation modules (EVMs) and development system cards will support concurrent engineering. Together, PE, Code Warrior and EVMs create a complete, scalable tools solution for easy, fast, and efficient development.

1.4 Product Documentation

The four documents listed in **Table 1-1** are required for a complete description of and proper design with the 56855. Documentation is available from local Freescale distributors, Freescale Semiconductor sales offices, Freescale Literature Distribution Centers, or online at **www.freescale.com**.

Topic Description		Order Number
56800E Reference Manual		
DSP56855 User's Manual	Detailed description of memory, peripherals, and interfaces of the 56855	DSP5685xUM
56855Electrical and timing specifications, pin descriptions, and package descriptions (this document)		56855
DSP56855 Details any chip issues that might be present Errata		DSP56855E

Table 1-1 56855 Chip Documentation

1.5 Data Sheet Conventions

This data sheet uses the following conventions:

OVERBAR	This is used to indicate a signal that is active when pulled low. For example, the $\overline{\text{RESET}}$ pin is active when low.			
"asserted"	A high true (active high) sig	nal is high or a low	true (active low) signal is low.	
"deasserted"	A high true (active high) sig	nal is low or a low t	rue (active low) signal is high.	
Examples:	Signal/Symbol	Logic State	Signal State	Voltage ¹
	PIN	True	Asserted	V _{IL} /V _{OL}
	PIN	False	Deasserted	V _{IH} /V _{OH}
	PIN	True	Asserted	V _{IH} /V _{OH}
	PIN	False	Deasserted	V _{IL} /V _{OL}

1. Values for VIL, VOL, VIH, and VOH are defined by individual product specifications.

Part 2 Signal/Connection Descriptions

2.1 Introduction

The input and output signals of the 56855 are organized into functional groups, as shown in **Table 2-1** and as illustrated in **Figure 2-1**. In **Table 3-1** each table row describes the package pin and the signal or signals present.

Functional Group	Number of Pins
Power (V _{DD,} V _{DDIO, or} V _{DDA})	(4, 10, 1) ¹
Ground (V_{SS} , V_{SSIO} , or V_{SSA})	(4, 10, 1) ¹
PLL and Clock	3
External Bus Signals	39
External Chip Select*	4
Interrupt and Program Control	7 ²
Enhanced Synchronous Serial Interface (ESSI0) Port*	6
Serial Communications Interface (SCI0) Ports*	2
Serial Communications Interface (SCI1) Ports*	2
Quad Timer Module Port*	1
JTAG/Enhanced On-Chip Emulation (EOnCE)	6

Table 2-1 56855 Functional Group Pin Allocations
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*Alternately, GPIO pins

V_{DD} = V_{DD CORE}, V_{SS} = V_{SS CORE}, V_{DDIO} = V_{DD IO}, V_{SSIO} = V_{SS IO}, V_{DDA} = V_{DD ANA}, V_{SSA} = V_{SS ANA}
 MODA, MODB and MODC can be used as GPIO after the bootstrap process has completed.

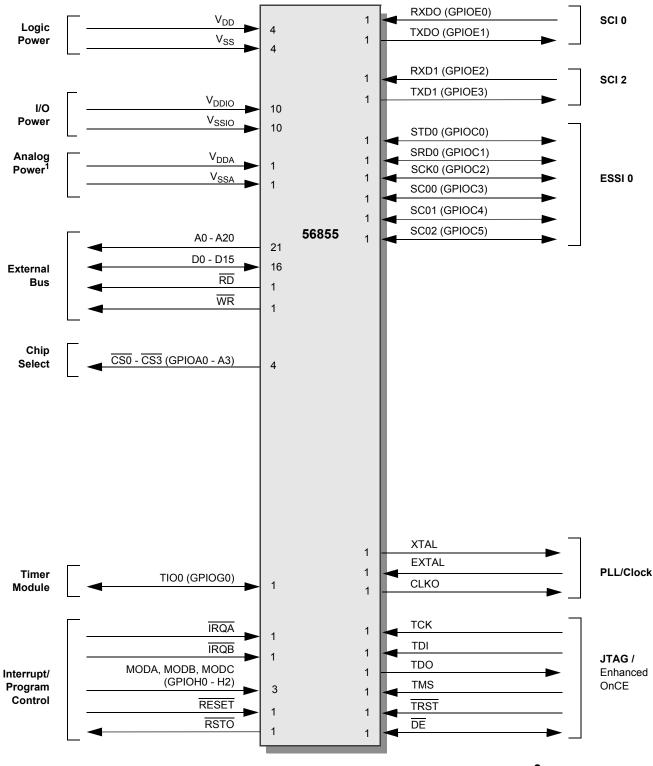


Figure 2-1 56855 Signals Identified by Functional Group²

1. Specifically for PLL, OSC, and POR.

2. Alternate pin functions are shown in parentheses.

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Part 3 Signals and Package Information

All digital inputs have a weak internal pull-up circuit associated with them. These pull-up circuits are enabled by default. Exceptions:

- 1. When a pin has GPIO functionality, the pull-up may be disabled under software control.
- 2. MODE A, MODE B and MODE C pins have no pull-up.
- 3. TCK has a weak pull-down circuit always active.
- 4. Bidirectional I/O pullups automatically disable when the output is enabled.

This table is presented consistently with the Signals Identified by Functional Group figure.

- 1. **BOLD** entries in the *Type* column represents the state of the pin just out of reset.
- 2. Output(Z) means an output in a High-Z condition.

Pin No.	Signal Name	Туре	Description
9	V _{DD}	V _{DD}	Power (V_{DD}) —These pins provide power to the internal structures of the chip, and should all be attached to V_{DD}
35	V _{DD}		chip, and should all be attached to v _{DD.}
65	V _{DD}		
84	V _{DD}		
10	V _{SS}	V _{SS}	Ground (V _{SS})—These pins provide grounding for the internal structures of the object of the objec
36	V _{SS}		the chip and should all be attached to V _{SS.}
66	V _{SS}		
85	V _{SS}		

Pin No.	Signal Name	Туре	Description
1	V _{DDIO}	V _{DDIO}	Power (V_{DDIO}) —These pins provide power for all I/O and ESD structures of the ship and about d all he attached to $V(r = (2, 2)/2)$
14	V _{DDIO}		the chip, and should all be attached to V_{DDIO} (3.3V).
29	V _{DDIO}		
43	V _{DDIO}		
49	V _{DDIO}		
58	V _{DDIO}		
72	V _{DDIO}		
76	V _{DDIO}		
86	V _{DDIO}		
96	V _{DDIO}		
2	V _{SSIO}	V _{SSIO}	Ground (V _{SSIO})—These pins provide grounding for all I/O and ESD
15	V _{SSIO}		structures of the chip and should all be attached to $V_{SS.}$
30	V _{SSIO}		
44	V _{SSIO}		
50	V _{SSIO}		
60	V _{SSIO}		
73	V _{SSIO}		
78	V _{SSIO}		
87	V _{SSIO}		
97	V _{SSIO}		
2	V _{SSIO}		
18	V _{DDA}	V _{DDA}	Analog Power (V _{DDA})—These pins supply an analog power source.
19	V _{SSA}	V _{SSA}	Analog Ground (V _{SSA})—This pin supplies an analog ground.

Table 3-1.	56855 Signal and	Package Information for th	e 100-pin LQFP (Continued)
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Pin No.	Signal Name	Туре	Description
5	A0	Output(Z)	Address Bus (A0-A20)—These signals specify a word address for external program or data memory access.
6	A1		program or data memory access.
7	A2		
8	A3		
22	A4		
23	A5		
24	A6		
25	A7		
31	A8		
32	A9		
33	A10		
34	A11		
45	A12		
46	A13		
47	A14		
48	A15		
53	A16		
54	A17		
55	A18		
56	A19		
57	A20		

Pin No.	Signal Name	Туре	Description
59	D0	Input/Output(Z)	Data Bus (D0-D15)—These pins provide the bidirectional data for external
67	D1		program or data memory accesses.
68	D2		
69	D3		
70	D4		
71	D5		
79	D6		
80	D7		
81	D8		
82	D9		
83	D10		
94	D11		
95	D12		
98	D13		
99	D14		
3	RD	Output	Read Enable (RD)— is asserted during external memory read cycles.
			This signal is pulled high during reset.
4	WR	Output	Write Enable (WR) — is asserted during external memory write cycles.
			This signal is pulled high during reset.
61	CS0	Output	External Chip Select (CS0)—This pin is used as a dedicated GPIO.
	GPIOA0	Input/Output	Port A GPIO (0) —This pin is a General Purpose I/O (GPIO) pin when not configured for host port usage.
62	CS1	Output	External Chip Select (CS1)—This pin is used as a dedicated GPIO.
	GPIOA1	Input/Output	Port A GPIO (1) —This pin is a General Purpose I/O (GPIO) pin when not configured for host port usage.
63	CS2	Output	External Chip Select (CS2)—This pin is used as a dedicated GPIO.
	GPIOA2	Input/Output	Port A GPIO (2) —This pin is a General Purpose I/O (GPIO) pin when not configured for host port usage.

Pin No.	Signal Name	Туре	Description
64	CS3	Output	External Chip Select (CS3)—This pin is used as a dedicated GPIO.
	GPIOA3	Input/Output	Port A GPIO (3) —This pin is a General Purpose I/O (GPIO) pin when not configured for host port usage.
77	TIO0	Input/Output	Timer Input/Output (TIO0) —This pin can be independently configured to be either timer input source or output flag.
	GPIOG0	Input/Output	Port G GPIO (0) —This pin is a General Purpose I/O (GPIO) pin that can individually be programmed as input or output pin.
16	IRQA	Input	External Interrupt Request A and B—The IRQA and IRQB inputs are
17	ĪRQB		asynchronized external interrupt requests that indicate that an external device is requesting service. A Schmitt trigger input is used for noise immunity. They can be programmed to be level-sensitive or negative-edge-triggered. If level-sensitive triggering is selected, an external pull-up resistor is required for Wired-OR operation.
11	MODA	Input	Mode Select (MODA)—During the bootstrap process MODA selects one of the eight bootstrap modes.
	GPIOH0	Input/Output	Port H GPIO (0) —This pin is a General Purpose I/O (GPIO) pin after the bootstrap process has completed.
12	MODB	Input	Mode Select (MODB) —During the bootstrap process MODB selects one of the eight bootstrap modes.
	GPIOH1	Input/Output	Port H GPIO (1) —This pin is a General Purpose I/O (GPIO) pin after the bootstrap process has completed.
13	MODC	Input	Mode Select (MODC)—During the bootstrap process MODC selects one of the eight bootstrap modes.
	GPIOH2	Input/Output	Port H GPIO (2) —This pin is a General Purpose I/O (GPIO) pin after the bootstrap process has completed.
28	RESET	Input	Reset (RESET) This input is a direct hardware reset on the processor. When RESET is asserted low, the device is initialized and placed in the Reset state. A Schmitt trigger input is used for noise immunity. When the RESET pin is deasserted, the initial chip operating mode is latched from the MODA, MODB, and MODC pins. To ensure complete hardware reset, RESET and TRST should be asserted
			together. The only exception occurs in a debugging environment when a hardware reset is required and it is necessary not to reset the JTAG/Enhanced OnCE module. In this case, assert RESET, but do not assert TRST.
27	RSTO	Output	Reset Output (RSTO) —This output is asserted on any reset condition (external reset, low voltage, software or COP).

Pin No.	Signal Name	Туре	Description
51	RXD0	Input	Serial Receive Data 0 (RXD0)—This input receives byte-oriented serial data and transfers it to the SCI 0 receive shift register.
	GPIOE0	Input/Output	Port E GPIO (0) —This pin is a General Purpose I/O (GPIO) pin that can individually be programmed as input or output pin.
52	TXD0	Output(Z)	Serial Transmit Data 0 (TXD0)—This signal transmits data from the SCI 0 transmit data register.
	GPIOE1	Input/Output	Port E GPIO (1) —This pin is a General Purpose I/O (GPIO) pin that can individually be programmed as input or output pin.
74	RXD1	Input	Serial Receive Data 1 (RXD1)—This input receives byte-oriented serial data and transfers it to the SCI 1 receive shift register.
	GPIOE2	Input/Output	Port E GPIO (2) —This pin is a General Purpose I/O (GPIO) pin that can individually be programmed as input or output pin.
75	TXD1	Output(Z)	Serial Transmit Data 1 (TXD1)—This signal transmits data from the SCI 1 transmit data register.
	GPIOE3	Input/Output	Port E GPIO (3) —This pin is a General Purpose I/O (GPIO) pin that can individually be programmed as input or output pin.
88	STD0	Output	ESSI Transmit Data (STD0) —This output pin transmits serial data from the ESSI Transmitter Shift Register.
	GPIOC0	Input/Output	Port C GPIO (0) —This pin is a General Purpose I/O (GPIO) pin when the ESSI is not in use.
89	SRD0	Input	ESSI Receive Data (SRD0) —This input pin receives serial data and transfers the data to the ESSI Receive Shift Register.
	GPIOC1	Input/Output	Port C GPIO (1) —This pin is a General Purpose I/O (GPIO) pin when the ESSI is not in use.
90	SCK0	Input/Output	ESSI Serial Clock (SCK0) —This bidirectional pin provides the serial bit rate clock for the transmit section of the ESSI. The clock signal can be continuous or gated and can be used by both the transmitter and receiver in synchronous mode.
	GPIOC2	Input/Output	Port C GPIO (2) —This pin is a General Purpose I/O (GPIO) pin when the ESSI is not in use.

Pin No.	Signal Name	Туре	Description
91	SC00	Input/Output	ESSI Serial Control Pin 0 (SC00) —The function of this pin is determined by the selection of either synchronous or asynchronous mode. For asynchronous mode, this pin will be used for the receive clock I/O. For synchronous mode, this pin is used either for transmitter1 output or for serial I/O flag 0.
	GPIOC3	Input/Output	Port C GPIO (3) —This pin is a General Purpose I/O (GPIO) pin when the ESSI is not in use.
92	SC01	Input/Output	ESSI Serial Control Pin 1 (SC01) —The function of this pin is determined by the selection of either synchronous or asynchronous mode. For asynchronous mode, this pin is the receiver frame sync I/O. For synchronous mode, this pin is used either for transmitter2 output or for serial I/O flag 1.
	GPIOC4	Input/Output	Port C GPIO (4) —This pin is a General Purpose I/O (GPIO) pin when the ESSI is not in use.
93	SC02	Input/Output	ESSI Serial Control Pin 2 (SC02) —This pin is used for frame sync I/O. SC02 is the frame sync for both the transmitter and receiver in synchronous mode and for the transmitter only in asynchronous mode. When configured as an output, this pin is the internally generated frame sync signal. When configured as an input, this pin receives an external frame sync signal for the transmitter (and the receiver in synchronous operation).
	GPIOC5	Input or Output	Port C GPIO (5) —This pin is a General Purpose I/O (GPIO) pin when the ESSI is not in use.
20	XTAL	Input/ Output	Crystal Oscillator Output (XTAL) —This output connects the internal crystal oscillator output to an external crystal. If an external clock source other than a crystal oscillator is used, XTAL must be used as the input.
21	EXTAL	Input	External Crystal Oscillator Input (EXTAL) —This input should be connected to an external crystal. If an external clock source other than a crystal oscillator is used, EXTAL must be tied off. See Section 4.5.2
26	CLKO	Output	Clock Output (CLKO) —This pin outputs a buffered clock signal. When enabled, this signal is the system clock divided by four.
42	ТСК	Input	Test Clock Input (TCK) —This input pin provides a gated clock to synchronize the test logic and to shift serial data to the JTAG/Enhanced OnCE port. The pin is connected internally to a pull-down resistor.
40	TDI	Input	Test Data Input (TDI) —This input pin provides a serial input data stream to the JTAG/Enhanced OnCE port. It is sampled on the rising edge of TCK and has an on-chip pull-up resistor.
39	TDO	Output (Z)	Test Data Output (TDO) —This tri-statable output pin provides a serial output data stream from the JTAG/Enhanced OnCE port. It is driven in the Shift-IR and Shift-DR controller states, and changes on the falling edge of TCK.

Pin No.	Signal Name	Туре	Description
41	TMS	Input	Test Mode Select Input (TMS)—This input pin is used to sequence theJTAG TAP controller's state machine. It is sampled on the rising edge ofTCK and has an on-chip pull-up resistor.Note:Always tie the TMS pin to V _{DD} through a 2.2K resistor.
38	TRST	Input	Test Reset (TRST) —As an input, a low signal on this pin provides a reset signal to the JTAG TAP controller. To ensure complete hardware reset, TRST should be asserted whenever RESET is asserted. The only exception occurs in a debugging environment, since the Enhanced OnCE/JTAG module is under the control of the debugger. In this case it is not necessary to assert TRST when asserting RESET. Outside of a debugging environment RESET should be permanently asserted by grounding the signal, thus disabling the Enhanced OnCE/JTAG module on the device.
37	DE	Input/Output	 Debug Event (DE)—This is an open-drain, bidirectional, active low signal. As an input, it is a means of entering debug mode of operation from an external command controller. As an output, it is a means of acknowledging that the chip has entered debug mode. This pin is connected internally to a weak pull-up resistor.

Part 4 Specifications

4.1 General Characteristics

The 56855 is fabricated in high-density CMOS with 5-volt tolerant TTL-compatible digital inputs. The term "5-volt tolerant" refers to the capability of an I/O pin, built on a 3.3V compatible process technology, to withstand a voltage up to 5.5V without damaging the device. Many systems have a mixture of devices designed for 3.3V and 5V power supplies. In such systems, a bus may carry both 3.3V and 5V- compatible I/O voltage levels (a standard 3.3V I/O is designed to receive a maximum voltage of $3.3V \pm 10\%$ during normal operation without causing damage). This 5V tolerant capability therefore offers the power savings of 3.3V I/O levels while being able to receive 5V levels without being damaged.

Absolute maximum ratings given in Table 4-1 are stress ratings only, and functional operation at the maximum is not guaranteed. Stress beyond these ratings may affect device reliability or cause permanent damage to the device.

The 56855 DC/AC electrical specifications are preliminary and are from design simulations. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. Finalized

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specifications will be published after complete characterization and device qualifications have been completed.

CAUTION

This device contains protective circuitry to guard against damage due to high static voltage or electrical fields. However, normal precautions are advised to avoid application of any voltages higher than maximum rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate voltage level.

Characteristic	Symbol	Min	Max	Unit
Supply voltage, core	V _{DD} ¹	V _{SS} – 0.3	V _{SS} + 2.0	V
Supply voltage, IO Supply voltage, analog	V _{DDIO} ² V _{DDIO} ²	V _{SSIO} – 0.3 V _{SSA} – 0.3	V _{SSIO} + 4.0 V _{DDA} + 4.0	V
Digital input voltages Analog input voltages (XTAL, EXTAL)	V _{IN} V _{INA}	V _{SSIO} – 0.3 V _{SSA} – 0.3	V _{SSIO} + 5.5 V _{DDA} + 0.3	V
Current drain per pin excluding V _{DD} , GND	I	—	8	mA
Junction temperature	TJ	-40	120	°C
Storage temperature range	T _{STG}	-55	150	°C

Table 4-1 Absolute Maximum Ratings

1. V_{DD} must not exceed V_{DDIO}

2. V_{DDIO} and V_{DDA} must not differ by more that 0.5V

Table 4-2 Recommended Operating Conditions

Characteristic	Symbol	Min	Мах	Unit
Supply voltage for Logic Power	V _{DD}	1.62	1.98	V
Supply voltage for I/O Power	V _{DDIO}	3.0	3.6	V
Supply voltage for Analog Power	V _{DDA}	3.0	3.6	V

Characteristic	Symbol	Min	Max	Unit
Ambient operating temperature	T _A	-40	85	°C
PLL clock frequency ¹	f _{pll}	_	240	MHz
Operating Frequency ²	f _{op}	_	120	MHz
Frequency of peripheral bus	f _{ipb}		60	MHz
Frequency of external clock	f _{clk}	_	240	MHz
Frequency of oscillator	f _{osc}	2	4	MHz
Frequency of clock via XTAL	f _{xtal}	_	240	MHz
Frequency of clock via EXTAL	f _{extal}	2	4	MHz

Table 4-2 Recommended Operating Conditions

1. Assumes clock source is direct clock to EXTAL or crystal oscillator running 2-4MHz. PLL must be enabled, locked, and selected. The actual frequency depends on the source clock frequency and programming of the CGM module.

2. Master clock is derived from on of the following four sources:

 f_{clk} = f_{xtal} when the source clock is the direct clock to EXTAL

 $f_{clk} = f_{pll}$ when PLL is selected

 f_{clk} = f_{osc} when the source clock is the crystal oscillator and PLL is not selected

 f_{clk} = f_{extal} when the source clock is the direct clock to EXTAL and PLL is not selected

Table 4-3 Thermal Characteristics¹

Characteristic	100-pin LQFP					
Characteristic	Symbol	Value	Unit			
Thermal resistance junction-to-ambient (estimated)	θ_{JA}	41.2	°C/W			
I/O pin power dissipation	P _{I/O}	User Determined	W			
Power dissipation	P _D	$P_D = (I_DD \times V_DD) + P_I/O$	W			
Maximum allowed P _D	P _{DMAX}	$(T_J - T_A) / R\theta_{JA}^2$	°C			

1. See Section 6.1 for more detail.

2. TJ = Junction Temperature TA = Ambient Temperature

4.2 DC Electrical Characteristics

Table 4-4 DC Electrical Characteristics

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \leq 50 pF, \ f_{op} = 120 MHz$

Characteristic	Symbol	Min	Тур	Мах	Unit
Input high voltage (XTAL/EXTAL)	V _{IHC}	V _{DDA} – 0.8	V _{DDA}	V _{DDA} + 0.3	V
Input low voltage (XTAL/EXTAL)	V _{ILC}	-0.3	—	0.5	V
Input high voltage	V _{IH}	2.0	—	5.5	V
Input low voltage	V _{IL}	-0.3	—	0.8	V
Input current low (pullups disabled)	۱ _{IL}	-1	—	1	μA
Input current high (pullups disabled)	I _{IH}	-1	—	1	μA
Output tri-state current low	I _{OZL}	-10	—	10	μA
Output tri-state current high	I _{OZH}	-10	—	10	μA
Output High Voltage	V _{OH}	V _{DDIO} – 0.7	—	—	V
Output Low Voltage	V _{OL}	—	—	0.4	V
Output High Current	I _{OH}	8	—	16	mA
Output Low Current	I _{OL}	8	—	16	mA
Input capacitance	C _{IN}	—	8	—	pF
Output capacitance	C _{OUT}	—	12	—	pF
V _{DD} supply current (Core logic, memories, peripherals) Run ¹ Deep Stop ² Light Stop ³	I _{DD} ⁴		70 0.05 5	110 10 14	mA mA mA
V _{DDIO} supply current (I/O circuity) Run ⁵ Deep Stop ²	I _{DDIO}	_	40 0	50 1.5	mA mA
V _{DDA} supply current (analog circuity) Deep Stop ²	I _{DDA}		60	120	μA
Low Voltage Interrupt ⁶	V _{EI}	—	2.5	2.85	V
Low Voltage Interrupt Recovery Hysteresis	V _{EIH}		50		mV
Power on Reset ⁷	POR		1.5	2.0	V

Note: Run (operating) I_{DD} measured using external square wave clock source ($f_{osc} = 4MHz$) into XTAL. All inputs 0.2V from rail; no DC loads; outputs unloaded. All ports configured as inputs; measured with all modules enabled. PLL set to 240MHz out.

1. Running Core, performing 50% NOP and 50% FIR. Clock at 120 MHz.

- 2. Deep Stop Mode Operation frequency = 4 MHz, PLL set to 4 MHz, crystal oscillator and time of day module operating.
- 3. Light Stop Mode Operation frequency = 120 MHz, PLL set to 240 MHz, crystal oscillator and time of day module operating.
- 4. I_{DD} includes current for core logic, internal memories, and all internal peripheral logic circuitry.

5. Running core and performing external memory access. Clock at 120 MHz.

6. When V_{DD} drops below V_{EI} max value, an interrupt is generated.

7. Power-on reset occurs whenever the digital supply drops below 1.8V. While power is ramping up, this signal remains active for as long as the internal 2.5V is below 1.8V no matter how long the ramp up rate is. The internally regulated voltage is typically 100 mV less than V_{DD} during ramp up until 2.5V is reached, at which time it self-regulates.

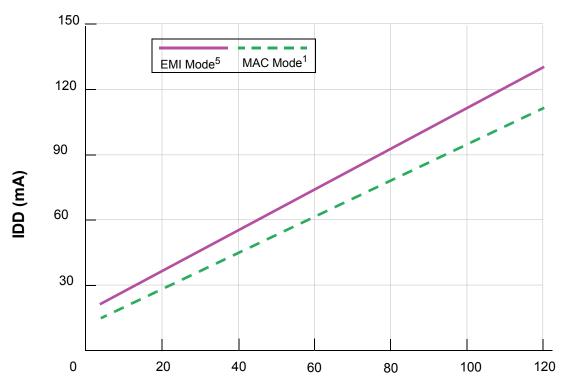
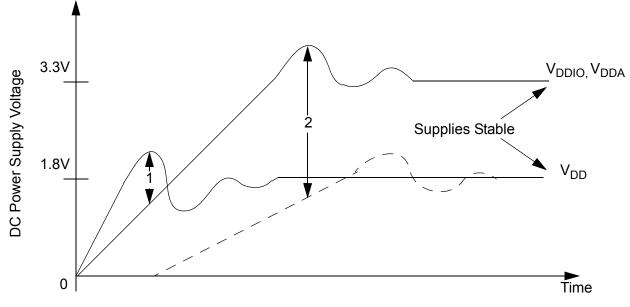


Figure 4-1 Maximum Run I_{DDTOTAL} vs. Frequency (see Notes 1. and 5. in Table 4-4)

4.3 Supply Voltage Sequencing and Separation Cautions

Figure 4-2 shows two situations to avoid in sequencing the V_{DD} and V_{DDIO} , V_{DDA} supplies.



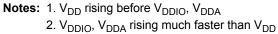


Figure 4-2 Supply Voltage Sequencing and Separation Cautions

 V_{DD} should not be allowed to rise early (1). This is usually avoided by running the regulator for the V_{DD} supply (1.8V) from the voltage generated by the 3.3V V_{DDIO} supply, see Figure 4-3. This keeps V_{DD} from rising faster than V_{DDIO} .

 V_{DD} should not rise so late that a large voltage difference is allowed between the two supplies (2). Typically this situation is avoided by using external discrete diodes in series between supplies, as shown in **Figure 4-3**. The series diodes forward bias when the difference between V_{DDIO} and V_{DD} reaches approximately 2.1, causing V_{DD} to rise as V_{DDIO} ramps up. When the V_{DD} regulator begins proper operation, the difference between supplies will typically be 0.8V and conduction through the diode chain reduces to essentially leakage current. During supply sequencing, the following general relationship should be adhered to:

 $V_{DDIO} \geq V_{DD} \geq (V_{DDIO} - 2.1V)$

In practice, V_{DDA} is typically connected directly to V_{DDIO} with some filtering.

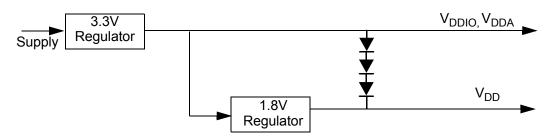
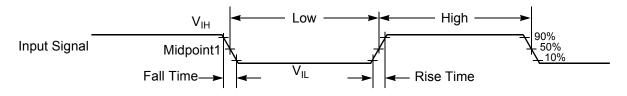


Figure 4-3 Example Circuit to Control Supply Sequencing

4.4 AC Electrical Characteristics

Timing waveforms in Section 4.2 are tested with a V_{IL} maximum of 0.8 V and a V_{IH} minimum of 2.0 V for all pins except XTAL, which is tested using the input levels in Section 4.2. In Figure 4-4 the levels of V_{IH} and V_{IL} for an input signal are shown.



Note: The midpoint is V_{IL} + $(V_{IH} - V_{IL})/2$.

Figure 4-4 Input Signal Measurement References

Figure 4-5 shows the definitions of the following signal states:

- Active state, when a bus or signal is driven, and enters a low impedance state.
- Tri-stated, when a bus or signal is placed in a high impedance state.
- Data Valid state, when a signal level has reached V_{OL} or V_{OH}.
- Data Invalid state, when a signal level is in transition between V_{OL} and V_{OH}.

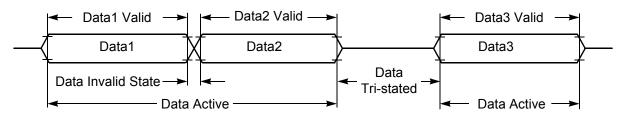


Figure 4-5 Signal State

4.5 External Clock Operation

The 56855 system clock can be derived from a crystal or an external system clock signal. To generate a reference frequency using the internal oscillator, a reference crystal must be connected between the EXTAL and XTAL pins.

4.5.1 Crystal Oscillator

The internal oscillator is designed to interface with a parallel-resonant crystal resonator in the frequency range specified for the external crystal in Table 4-5. In Figure 4-6 a typical crystal oscillator circuit is shown. Follow the crystal supplier's recommendations when selecting a crystal, because crystal parameters determine the component values required to provide maximum stability and reliable start-up. The crystal and associated components should be mounted as close as possible to the EXTAL and XTAL pins to minimize output distortion and start-up stabilization time.



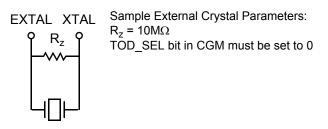


Figure 4-6 Crystal Oscillator

4.5.2 High Speed External Clock Source (> 4MHz)

The recommended method of connecting an external clock is given in Figure 4-7. The external clock source is connected to XTAL and the EXTAL pin is held at ground, V_{DDA} , or $V_{DDA}/2$. The TOD_SEL bit in CGM must be set to 0.

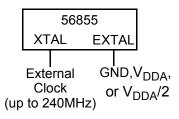


Figure 4-7 Connecting a High Speed External Clock Signal using XTAL

4.5.3 Low Speed External Clock Source (2-4MHz)

The recommended method of connecting an external clock is given in Figure 4-8. The external clock source is connected to XTAL and the EXTAL pin is held at $V_{DDA}/2$. The TOD_SEL bit in CGM must be set to 0.

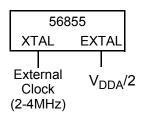


Figure 4-8 Connecting a Low Speed External Clock Signal using XTAL

Table 4-5 External Clock Operation Timing Requirements⁴

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \leq 50 pF, \ f_{op} = 120 MHz$

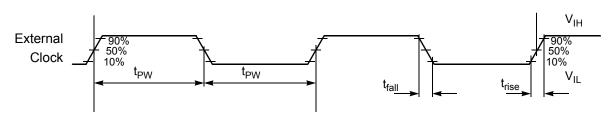
Characteristic	Symbol	Min	Тур	Мах	Unit
Frequency of operation (external clock driver) ¹	f _{osc}	0		240	MHz
Clock Pulse Width ⁴	t _{PW}	6.25	_	_	ns
External clock input rise time ^{2, 4}	t _{rise}	_	_	TBD	ns
External clock input fall time ^{3, 4}	t _{fall}	_	_	TBD	ns

1. See Figure 4-7 for details on using the recommended connection of an external clock driver.

2. External clock input rise time is measured from 10% to 90%.

3. External clock input fall time is measured from 90% to 10%.

4. Parameters listed are guaranteed by design.



Note: The midpoint is $V_{IL} + (V_{IH} - V_{IL})/2$.

Figure 4-9 External Clock Timing

Table 4-6 PLL Timing

					- I.
Characteristic	Symbol	Min	Тур	Мах	Unit
External reference crystal frequency for the PLL ¹	f _{osc}	2	4	4	MHz
PLL output frequency	f _{clk}	40		240	MHz
PLL stabilization time ²	t _{plls}	_	1	10	ms

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \le 50 pF, \ f_{op} = 120 MHz$

1. An externally supplied reference clock should be as free as possible from any phase jitter for the PLL to work correctly. The PLL is optimized for 4MHz input crystal.

2. This is the minimum time required after the PLL setup is changed to ensure reliable operation.

4.6 External Memory Interface Timing

The External Memory Interface is designed to access static memory and peripheral devices. Figure 4-10 shows sample timing and parameters that are detailed in Table 4-7.

The timing of each parameter consists of both a fixed delay portion and a clock related portion; as well as user controlled wait states. The equation:

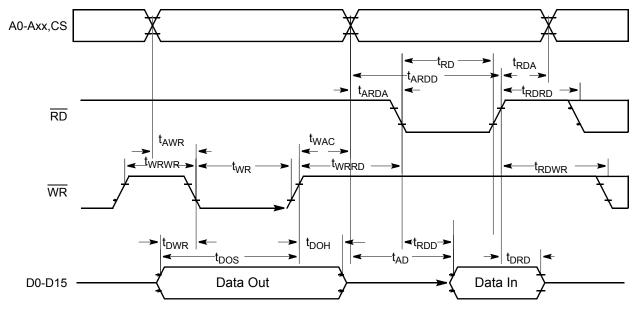
t = D + P * (M + W)

should be used to determine the actual time of each parameter. The terms in the above equation are defined as:

- t parameter delay time
- D fixed portion of the delay, due to on-chip path delays.
- P the period of the system clock, which determines the execution rate of the part (i.e. when the device is operating at 120 MHz, P = 8.33 ns).
- M Fixed portion of a clock period inherent in the design. This number is adjusted to account for possible clock duty cycle derating.
- W the sum of the applicable wait state controls. See the "Wait State Controls" column of **Table 4-7** for the applicable controls for each parameter. See the EMI chapter of the 83x Peripheral Manual for details of what each wait state field controls.

Some of the parameters contain two sets of numbers. These parameters have two different paths and clock edges that must be considered. Check both sets of numbers and use the smaller result. The appropriate entry may change if the operating frequency of the part changes.

The timing of write cycles is different when WWS = 0 than when WWS > 0. Therefore, some parameters contain two sets of numbers to account for this difference. The "Wait States Configuration" column of Table 4-7 should be used to make the appropriate selection.



Note: During read-modify-write instructions and internal instructions, the address lines do not change state.

Figure 4-10 External Memory Interface Timing

Table 4-7 External Memory Interface Timing

Operating Conditions: $V_{SS} = V_{SSIO} = V_{SSA} = 0 V$, $V_{DD} = 1.62 - 1.98 V$, $V_{DDIO} = V_{DDA} = 3.0 - 3.6V$, $T_A = -40 \times to + 120 \times C$, $C_L \pm 50 pF$, $P = 8.333 ns = 0.00 \times C_L \pm 100 \times$

Characteristic	Symbol	Wait States Configuration	D	М	Wait States Controls	Unit
Address Valid to WR Asserted	t _{AWR}	WWS=0	-0.79	0.50	wwss	ns
	AWR	WWS>0	-1.98	0.69		115
\overline{WR} Width Asserted to \overline{WR}	t _{WR}	WWS=0	-0.86	0.19	wws	ns
Deasserted	WR	WWS>0	-0.01	0.00		115
Data Out Valid to WR Asserted		WWS=0	-1.52	0.00		
	t _{DWR}	WWS=0	- 5.69	0.25	- wwss	ns
		WWS>0	-2.10	0.19		
		WWS>0	-4.66	0.50		
Valid Data Out Hold Time after \overline{WR} Deasserted	t _{DOH}		-1.47	0.25	WWSH	ns
Valid Data Out Set Up Time to WR	taaa		-2.36	0.19	WWS,WWSS	ns
Deasserted	t _{DOS}		-4.67	0.50		
Valid Address after WR Deasserted	t _{WAC}		-1.60	0.25	WWSH	
RD Deasserted to Address Invalid	t _{RDA}		- 0.44	0.00	RWSH	ns

Table 4-7 External Memory Interface Timing (Continued)

Operating Conditions: $V_{SS} = V_{SSIO} = V_{SSA} = 0 V$, $V_{DD} = 1.62 - 1.98 V$, $V_{DDIO} = V_{DDA} = 3.0 - 3.6V$, $T_A = -40 \times to + 120 \times C$, $C_L \pm 50 pF$, P = 8.333 ns

Characteristic	Symbol	Wait States Configuration	D	М	Wait States Controls	Unit
Address Valid to RD Deasserted	t _{ARDD}		-2.07	1.00	RWSS,RWS	ns
Valid Input Data Hold after RD Deasserted	t _{DRD}		0.00	N/A ¹	_	ns
RD Assertion Width	t _{RD}		-1.34	1.00	RWS	ns
Address Valid to Input Data Valid	t _{AD}		-10.27	1.00		ns
			-13.5	1.19	RWSS,RWS	115
Address Valid to RD Asserted	t _{ARDA}		- 0.94	0.00	RWSS	ns
RD Asserted to Input Data Valid	+		-9.53	1.00		ns
•	t _{RDD}		-12.64	1.19	RWSS,RWS	115
WR Deasserted to RD Asserted	t _{WRRD}		-0.75	0.25	WWSH,RWSS	ns
RD Deasserted to RD Asserted	t _{RDRD}		-0.16 ²	0.00	RWSS,RWSH	ns
WR Deasserted to WR Asserted	t	WWS=0	-0.44	0.75	WWSS, WWSH	20
	t _{wrwr}	WWS>0	-0.11	1.00		ns
RD Deasserted to WR Asserted	t _{RDWR}		0.14	0.50	MDAR, BMDAR,	ns
	YRDWR		-0.57	0.69	RWSH, WWSS	115

1. N/A since device captures data before it deasserts RD

2. If RWSS = RWSH = 0, RD does not deassert during back-to-back reads and D=0.00 should be used.

4.7 Reset, Stop, Wait, Mode Select, and Interrupt Timing

Table 1. Reset, Stop, Wait, Mode Select, and Interrupt Timing^{1, 2}

Operating Conditions: $V_{SS} = V_{SSIO} = V_{SSA} = 0$ V, $V_{DD} = 1.62 - 1.98$ V, $V_{DDIO} = V_{DDA} = 3.0 - 3.6$ V, $T_A = -40^{\circ}$ to $+120^{\circ}$ C, $C_L \le 50$ pF, $f_{op} = 120$ MHz

Characteristic	Symbol	Min	Max	Unit	See Figure
RESET Assertion to Address, Data and Control Signals High Impedance	t _{RAZ}	_	11	ns	4-11
Minimum RESET Assertion Duration ³	t _{RA}	30	_	ns	4-11
RESET Deassertion to First External Address Output	t _{RDA}	_	120T	ns	4-11
Edge-sensitive Interrupt Request Width	t _{IRW}	1T + 3	_	ns	4-12

Table 1. Reset, Stop, Wait, Mode Select, and Interrupt Timing^{1, 2} (Continued)

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \leq 50 p F, \ f_{op} = 120 M Hz$

					•
Characteristic	Symbol	Min	Мах	Unit	See Figure
IRQA, IRQB Assertion to External Data Memory Access Out Valid, caused by first instruction execution in the interrupt service routine	t _{IDM}	18T	_	ns	4-13
	t _{IDM -FAST}	14T	—		
IRQA, IRQB Assertion to General Purpose Output Valid, caused by first instruction execution in the interrupt service routine	t _{IG}	18T	—	ns	4-13
	t _{IG -FAST}	14T	—		
IRQA Low to First Valid Interrupt Vector Address Out recovery from Wait State ⁴	t _{IRI}	22T	_	ns	4-14
	t _{IRI -FAST}	18T	—		
Delay from $\overline{\text{IRQA}}$ Assertion (exiting Stop) to External Data Memory^5	t _{IVV}	1.5T	_	ns	4-15
Delay from IRQA Assertion (exiting Wait) to External Data Memory	t _{IF}				4-15
Fast ⁶ Normal ⁷		18T 22ET		ns ns	
RSTO pulse width ⁸ normal operation internal reset mode	t _{RSTO}	128ET 8ET			4-16

1. In the formulas, T = clock cycle. For f_{op} = 120MHz operation and f_{ipb} = 60MHz, T = 8.33ns.

2. Parameters listed are guaranteed by design.

3. At reset, the PLL is disabled and bypassed. The part is then put into Run mode and t_{clk} assumes the period of the source clock, t_{xtal} , t_{extal} or t_{osc} .

4. The minimum is specified for the duration of an edge-sensitive IRQA interrupt required to recover from the Stop state. This is not the minimum required so that the IRQA interrupt is accepted.

5. The interrupt instruction fetch is visible on the pins only in Mode 3.

6. Fast stop mode:

Fast stop recovery applies when external clocking is in use (direct clocking to XTAL) or when fast stop mode recovery is requested (OMR bit 6 is set to 1). In both cases the PLL and the master clock are unaffected by stop mode entry. Recovery takes one less cycle and t_{clk} will continue same value it had before stop mode was entered.

7. Normal stop mode:

As a power saving feature, normal stop mode disables and bypasses the PLL. Stop mode will then shut down the master clock, recovery will take an extra cycle (to restart the clock), and t_{clk} will resume at the input clock source rate.

8. ET = External Clock period, For an external crystal frequency of 8MHz, ET=125 ns.

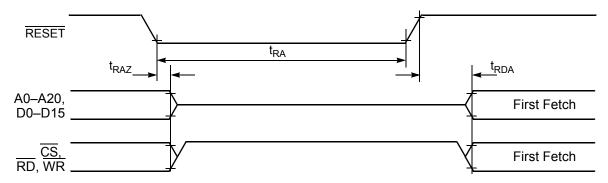


Figure 4-11 Asynchronous Reset Timing

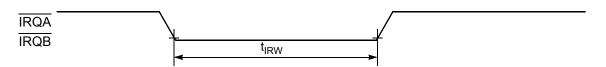


Figure 4-12 External Interrupt Timing (Negative-Edge-Sensitive)

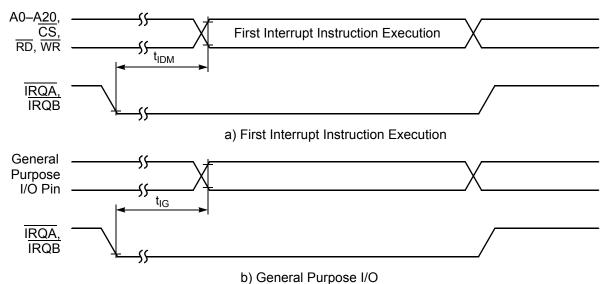


Figure 4-13 External Level-Sensitive Interrupt Timing

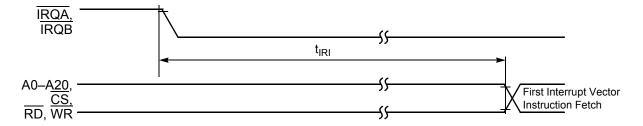


Figure 4-14 Interrupt from Wait State Timing

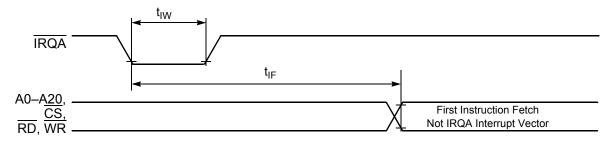


Figure 4-15 Recovery from Stop State Using Asynchronous Interrupt Timing



Figure 4-16 Reset Output Timing

4.8 Host Interface Port

Table 4-8 Host Interface Port Timing¹

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 \\ V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 \\ V, \ T_A = -40^\circ \ to + 120^\circ \\ C, \ C_L \leq 50 \\ pF, \ f_{op} = 120 \\ MHz$

Characteristic	Symbol	Min	Мах	Unit	See Figure
Access time	TACKDV	_	13	ns	4-17
Disable time	TACKDZ	3	—	ns	4-17
Time to disassert	TACKREQH	3.5	9	ns	4-17 4-20
Lead time	TREQACKL	0	—	ns	4-17 4-20

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Table 4-8 Host Interface Port Timing¹ (Continued)

Operating Conditions: $V_{SS} = V_{SSIO} = V_{SSA} = 0 V$, $V_{DD} = 1.62 - 1.98V$, $V_{DDIO} = V_{DDA} = 3.0 - 3.6V$, $T_A = -40^{\circ}$ to $+120^{\circ}$ C, $C_L \le 50$ pF, $f_{op} = 120$ MHz

Characteristic	Symbol	Min	Max	Unit	See Figure
Access time	TRADV	_	13	ns	4-18 4-19
Disable time	TRADX	5	_	ns	4-18 4-19
Disable time	TRADZ	3	_	ns	4-18 4-19
Setup time	TDACKS	3	—	ns	4-20
Hold time	TACKDH	1	—	ns	4-20
Setup time	TADSS	3	_	ns	4-21 4-23
Hold time	TDSAH	1	_	ns	4-21 4-22
Pulse width	TWDS	5	—	ns	4-21 4-22
Time to re-assert 1. After second write in 16-bit mode 2. After first write in 16-bit mode or after write in 8-bit mode	TACKREQL	4T + 5 5	5T + 9 13	ns ns	4-17 4-20

1. The formulas: T = clock cycle. f ipb = 60MHz, T = 16.7ns.

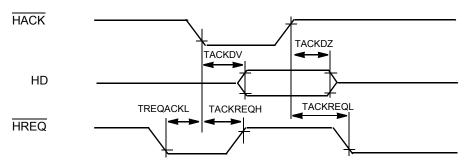


Figure 4-17 Controller-to-Host DMA Read Mode

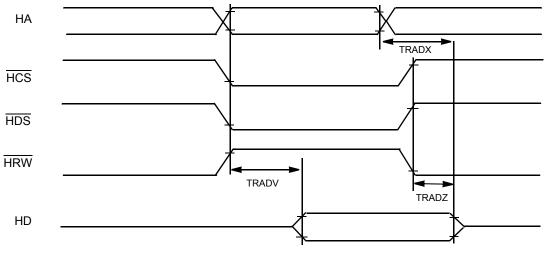


Figure 4-18 Single Strobe Read Mode

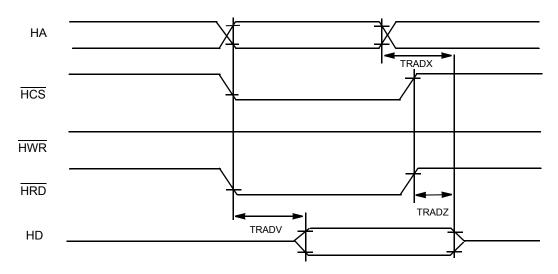
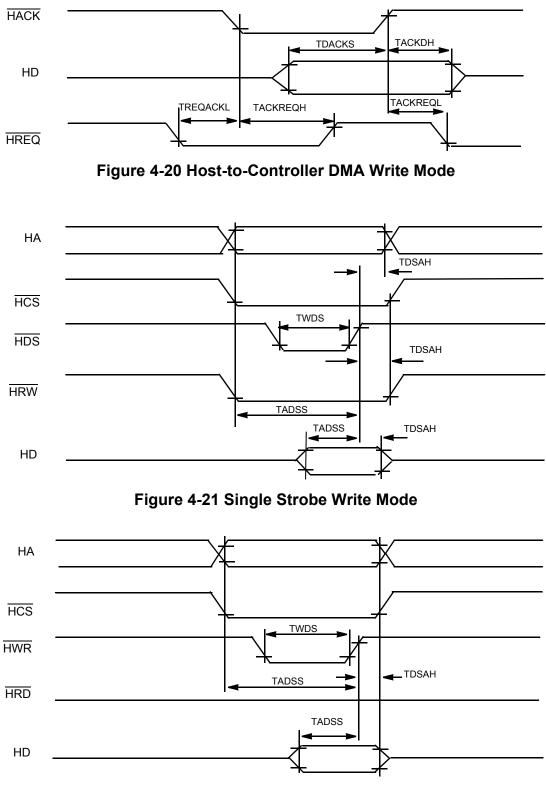


Figure 4-19 Dual Strobe Read Mode





4.9 Quad Timer Timing

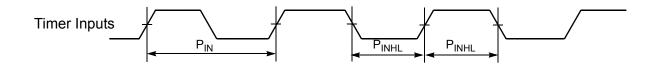
Table 4-9 Quad Timer Timing^{1, 2}

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 \\ V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 \\ V, \ T_A = -40^\circ \ to \ +120^\circ \\ C, \ C_L \leq 50 \\ pF, \ f_{op} = 120 \\ MHz$

Characteristic	Symbol	Min	Мах	Unit
Timer input period	P _{IN}	2T + 3		ns
Timer input high/low period	P _{INHL}	1T + 3	—	ns
Timer output period	P _{OUT}	2T - 3	—	ns
Timer output high/low period	P _{OUTHL}	1T - 3	—	ns

1. In the formulas listed, T = clock cycle. For f_{op} = 120MHz operation and fipb = 60MHz, T = 8.33ns.

2. Parameters listed are guaranteed by design.



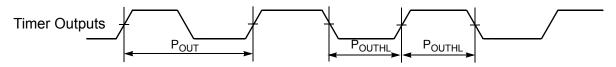


Figure 4-23 Timer Timing

4.10 Enhanced Synchronous Serial Interface (ESSI) Timing

Table 4-10 ESSI Master Mode¹ Switching Characteristics

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to \ +120^{\circ} C, \ C_L \leq 50 pF, \ f_{op} = 120 MHz$

Parameter	Symbol	Min	Тур	Мах	Units			
SCK frequency	fs	—	—	15 ²	MHz			
SCK period ³	t _{scкw}	66.7	—	—	ns			
SCK high time	t _{SCKH}	33.4 ⁴	—	—	ns			
SCK low time	t _{SCKL}	33.4 ⁴	_	_	ns			
Output clock rise/fall time	—	_	4		ns			
Delay from SCK high to SC2 (bl) high - Master ⁵	t _{TFSBHM}	-1.0	_	1.0	ns			
Delay from SCK high to SC2 (wl) high - Master ⁵	t _{TFSWHM}	-1.0	_	1.0	ns			
Delay from SC0 high to SC1 (bl) high - Master ⁵	t _{RFSBHM}	-1.0	_	1.0	ns			
Delay from SC0 high to SC1 (wl) high - Master ⁵	t _{RFSWHM}	-1.0	—	1.0	ns			
Delay from SCK high to SC2 (bl) low - Master ⁵	t _{TFSBLM}	-1.0	_	1.0	ns			
Delay from SCK high to SC2 (wl) low - Master ⁵	t _{TFSWLM}	-1.0	—	1.0	ns			
Delay from SC0 high to SC1 (bl) low - Master ⁵	t _{RFSBLM}	-1.0	_	1.0	ns			
Delay from SC0 high to SC1 (wl) low - Master ⁵	t _{RFSWLM}	-1.0	_	1.0	ns			
SCK high to STD enable from high impedance - Master	t _{TXEM}	-0.1	—	2	ns			
SCK high to STD valid - Master	t _{TXVM}	-0.1	_	2	ns			
SCK high to STD not valid - Master	t _{TXNVM}	-0.1	—	—	ns			
SCK high to STD high impedance - Master	t _{TXHIM}	-4	—	0	ns			
SRD Setup time before SC0 low - Master	t _{SM}	4	—	—	ns			
SRD Hold time after SC0 low - Master	t _{HM}	4	_	_	ns			
Synchronous Operation (in addition to standard internal clock parameters)								
SRD Setup time before SCK low - Master	t _{TSM}	4	_	_	ns			
SRD Hold time after SCK low - Master	t _{THM}	4	_	—	ns			

1. Master mode is internally generated clocks and frame syncs

2. Max clock frequency is IP_clk/4 = 60MHz / 4 = 15MHz for an 120MHz part.

3. All the timings for the ESSI are given for a non-inverted serial clock polarity (TSCKP=0 in SCR2 and RSCKP=0 in SCSR) and a non-inverted frame sync (TFSI=0 in SCR2 and RFSI=0 in SCSR). If the polarity of the clock and/or the frame sync have been inverted, all the timings remain valid by inverting the clock signal SCK/SC0 and/or the frame sync SC2/SC1 in the tables and in the figures.

- 4. 50 percent duty cycle
- 5. bl = bit length; wl = word length

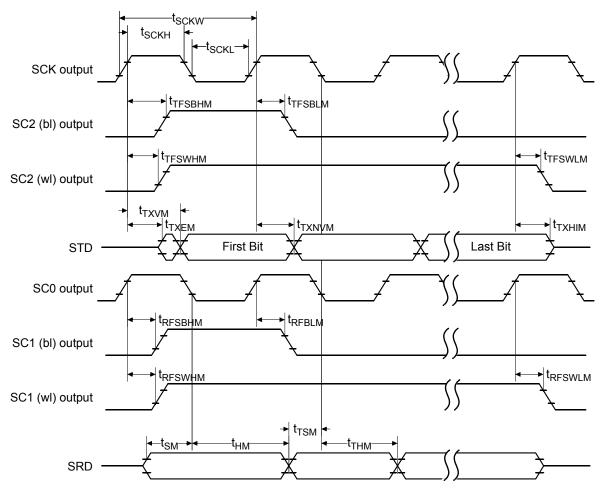


Figure 4-24 Master Mode Timing Diagram

Parameter	Symbol	Min	Тур	Мах	Units
SCK frequency	fs	_	—	15 ²	MHz
SCK period ³	t _{scкw}	66.7	—	—	ns
SCK high time	t _{scкн}	33.4 ⁴	—	—	ns
SCK low time	t _{SCKL}	33.4 ⁴	—	—	ns
Output clock rise/fall time	—	_	4	_	ns
Delay from SCK high to SC2 (bl) high - Slave ⁵	t _{TFSBHS}	-1	—	29	ns
Delay from SCK high to SC2 (wl) high - Slave ⁵	t _{TFSWHS}	-1	_	29	ns
Delay from SC0 high to SC1 (bl) high - Slave ⁵	t _{RFSBHS}	-1	—	29	ns
Delay from SC0 high to SC1 (wl) high - Slave ⁵	t _{RFSWHS}	-1	—	29	ns
Delay from SCK high to SC2 (bl) low - Slave ⁵	t _{TFSBLS}	-29	—	29	ns
Delay from SCK high to SC2 (wl) low - Slave ⁵	t _{TFSWLS}	-29	—	29	ns
Delay from SC0 high to SC1 (bl) low - Slave ⁵	t _{RFSBLS}	-29	—	29	ns
Delay from SC0 high to SC1 (wl) low - Slave ⁵	t _{RFSWLS}	-29	—	29	ns
SCK high to STD enable from high impedance - Slave	t _{TXES}	_	—	15	ns
SCK high to STD valid - Slave	t _{TXVS}	4	—	15	ns
SC2 high to STD enable from high impedance (first bit) - Slave	t _{FTXES}	4	—	15	ns
SC2 high to STD valid (first bit) - Slave	t _{FTXVS}	4	—	15	ns
SCK high to STD not valid - Slave	t _{TXNVS}	4	—	15	ns
SCK high to STD high impedance - Slave	t _{TXHIS}	4	—	15	ns
SRD Setup time before SC0 low - Slave	t _{SS}	4	—	—	ns
SRD Hold time after SC0 low - Slave	t _{HS}	4	—	_	ns
Synchronous Operation (in addition to standard external clock parameters)					
SRD Setup time before SCK low - Slave	t _{TSS}	4	_		ns
SRD Hold time after SCK low - Slave	t _{THS}	4	_	_	ns

Table 4-11 ESSI Slave Mode¹ Switching Characteristics

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \leq 50 pF, \ f_{op} = 120 MHz$

1. Slave mode is externally generated clocks and frame syncs

2. Max clock frequency is IP_clk/4 = 60MHz / 4 = 15MHz for a 120MHz part.

3. All the timings for the ESSI are given for a non-inverted serial clock polarity (TSCKP=0 in SCR2 and RSCKP=0 in SCSR) and a non-inverted frame sync (TFSI=0 in SCR2 and RFSI=0 in SCSR). If the polarity of the clock and/or the frame sync have been inverted, all the timings remain valid by inverting the clock signal SCK/SC0 and/or the frame sync SC2/SC1 in the tables and in the figures.

- 4. 50 percent duty cycle
- 5. bl = bit length; wl = word length

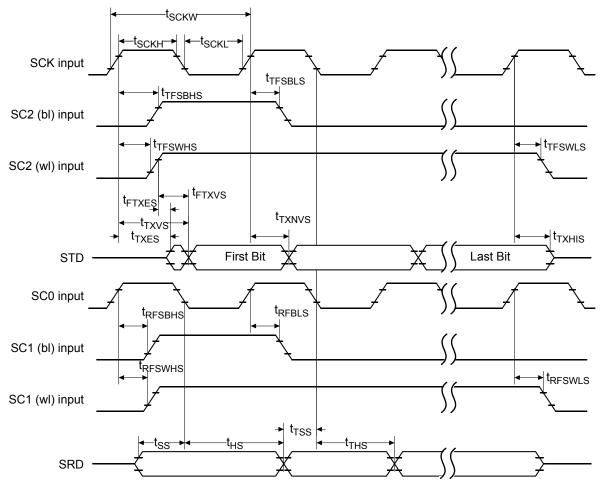


Figure 4-25 Slave Mode Clock Timing

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4.11 Serial Communication Interface (SCI) Timing

Table 4-12 SCI Timing⁴

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \le 50 pF, \ f_{op} = 120 MHz$

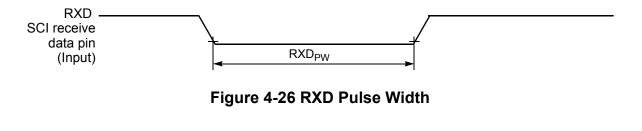
Characteristic	Symbol	Min	Мах	Unit
Baud Rate ¹	BR	_	(f _{MAX})/(32)	Mbps
RXD ² Pulse Width	RXD _{PW}	0.965/BR	1.04/BR	ns
TXD ³ Pulse Width	TXD _{PW}	0.965/BR	1.04/BR	ns

1. f_{MAX} is the frequency of operation of the system clock in MHz.

2. The RXD pin in SCI0 is named RXD0 and the RXD pin in SCI1 is named RXD1.

3. The TXD pin in SCI0 is named TXD0 and the TXD pin in SCI1 is named TXD1.

4. Parameters listed are guaranteed by design.



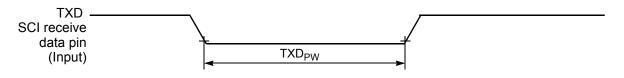


Figure 4-27 TXD Pulse Width

4.12 JTAG Timing

Table 4-13 JTAG Timing^{1, 3}

 $Operating \ Conditions: \ V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \leq 50 pF, \ f_{op} = 120 MHz$

Characteristic	Symbol	Min	Max	Unit
TCK frequency of operation ²	f _{OP}	DC	30	MHz
TCK cycle time	t _{CY}	33.3	_	ns
TCK clock pulse width	t _{PW}	16.6	_	ns
TMS, TDI data setup time	t _{DS}	3	_	ns
TMS, TDI data hold time	t _{DH}	3		ns
TCK low to TDO data valid	t _{DV}	—	12	ns
TCK low to TDO tri-state	t _{TS}	—	10	ns
TRST assertion time	t _{TRST}	35		ns
DE assertion time	t _{DE}	4T		ns

1. Timing is both wait state and frequency dependent. For the values listed, T = clock cycle. For 120MHz operation, T = 8.33ns.

2. TCK frequency of operation must be less than 1/4 the processor rate.

3. Parameters listed are guaranteed by design.

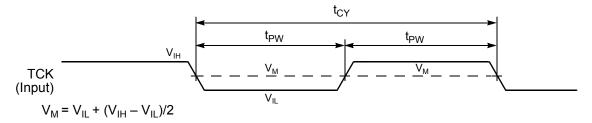
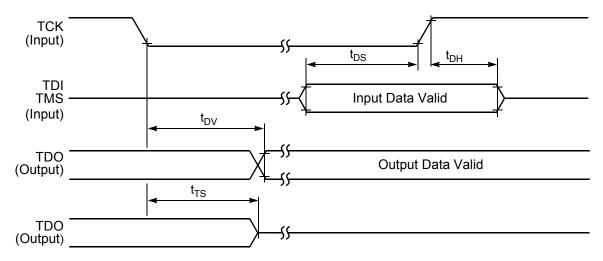


Figure 4-28 Test Clock Input Timing Diagram





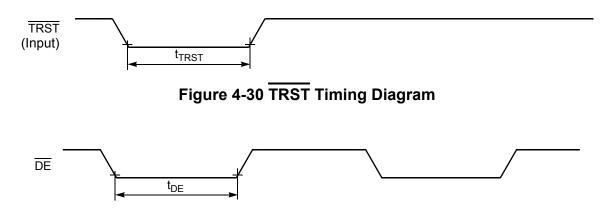


Figure 4-31 Enhanced OnCE—Debug Event

4.13 GPIO Timing

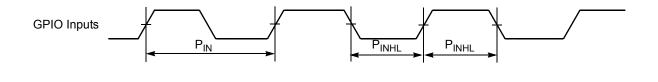
Table 4-14 GPIO Timing^{1, 2}

 $Operating \ Conditions: V_{SS} = V_{SSIO} = V_{SSA} = 0 \ V, \ V_{DD} = 1.62 - 1.98 V, \ V_{DDIO} = V_{DDA} = 3.0 - 3.6 V, \ T_A = -40^{\circ} \ to + 120^{\circ} C, \ C_L \leq 50 pF, \ f_{op} = 120 MHz$

Characteristic	Symbol	Min	Max	Unit
GPIO input period	P _{IN}	2T + 3		ns
GPIO input high/low period	P _{INHL}	1T + 3	—	ns
GPIO output period	P _{OUT}	2T - 3	—	ns
GPIO output high/low period	POUTHL	1T - 3	—	ns

1. In the formulas listed, T = clock cycle. For f_{op} = 120MHz operation and fipb = 60MHz, T = 8.33ns

2. Parameters listed are guaranteed by design.



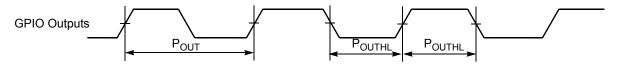


Figure 4-32 GPIO Timing

Part 5 Packaging

5.1 Package and Pin-Out Information 56855

This section contains package and pin-out information for the 100-pin LQFP configuration of the 56855.

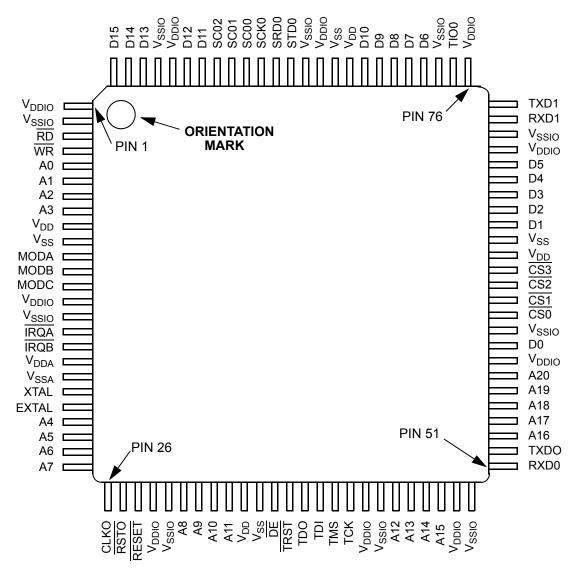
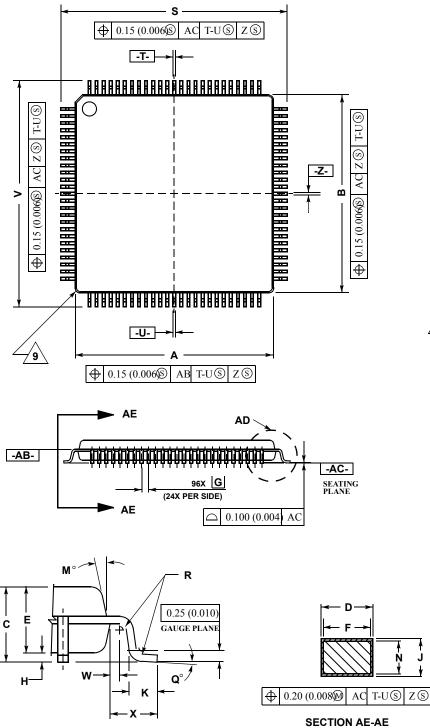


Figure 5-1 Top View, 56855 100-pin LQFP Package

Pin No.	Signal Name						
1	V _{DDIO}	26	CLKO	51	RXD0	76	V _{DDIO}
2	V _{SSIO}	27	RSTO	52	TXD0	77	TIO0
3	RD	28	RESET	53	A16	78	V _{SSIO}
4	WR	29	V _{DDIO}	54	A17	79	D6
5	A0	30	V _{SSIO}	55	A18	80	D7
6	A1	31	A8	56	A19	81	D8
7	A2	32	A9	57	A20	82	D9
8	A3	33	A10	58	V _{DDIO}	83	D10
9	V _{DD}	34	A11	59	D0	84	V _{DD}
10	V _{SS}	35	V _{DD}	60	V _{SSIO}	85	V _{SS}
11	MODA	36	V _{SS}	61	CS0	86	V _{DDIO}
12	MODB	37	DE	62	CS1	87	V _{SSIO}
13	MODC	38	TRST	63	CS2	88	STD0
14	V _{DDIO}	39	TDO	64	CS3	89	SRD0
15	V _{SSIO}	40	TDI	65	V _{DD}	90	SCK0
16	IRQA	41	TMS	66	V _{SS}	91	SC00
17	IRQB	42	ТСК	67	D1	92	SC01
18	V _{DDA}	43	V _{DDIO}	68	D2	93	SC02
19	V _{SSA}	44	V _{SSIO}	69	D3	94	D11
20	XTAL	45	A12	70	D4	95	D12
21	EXTAL	46	A13	71	D5	96	V _{DDIO}
22	A4	47	A14	72	V _{DDIO}	97	V _{SSIO}
23	A5	48	A15	73	V _{SSIO}	98	D13
24	A6	49	V _{DDIO}	74	RXD1	99	D14
25	A7	50	V _{SSIO}	75	TXD1	100	D15

Table 5-1 56855 Pin Identification By Pin Number

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NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER. DATUM PLANE -AB- IS LOCATED AT BOTTOM 2 3 OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC
- BODY AT THE BOTTOM OF THE PARTING LINE DATUMS -T-, -U-, AND -Z- TO BE DETERMINED 4
- AT DATUM PLANE -AB-5 DIMENSIONS S AND V TO BE DETERMINED
- AT SEATING PLANE -AC-DIMENSIONS A AND B DO NOT INCLUDE 6 MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.250 (0.010) PER SIDE DIMENSIONS A AND B DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE - AB-
- DIMENSION D DOES NOT INCLUDE DAMBAR 7. PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE D DIMENSION TO EXCEED 0.350 (0.014). DAMBAR CAN NOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND AN ADJACENT LEAD IS 0.070 (0.003).
- MINIMUM SOLDER PLATE THICKNESS SHALL BE 0 0076 (0 003)
- EXACT SHAPE OF EACH CORNER MAY VARY 9. FROM DEPICTION.

	MILL	IMETE	RS INCHES		
DIN	I MIN	MAX	MIN	MAX	
Α	13.950	14.050	0.549	0.553	
В	13.950	14.050	0.549	0.553	
С	1.400	1.600	0.055	0.063	
D	0.170	0.270	0.007	0.011	
E	1.350	1.450	0.053	0.057	
F	0.170	0.230	0.007	0.009	
G	0.500 BSC		0.020) BSC	
Н	0.050	0.150	0.002	0.006	
J	0.090	0.200	0.004	0.008	
K	0.500	0.700	0.020	0.028	
Μ	12°	REF	12° REF		
N	0.090	0.160	0.004	0.006	
0	1°	5°	1°	5°	
R	0.150	0.250	0.006	0.010	
S	15.950	16.050	0.628	0.632	
V	15.950	16.050	0.628	0.632	
W	0.20) REF	0.008 REF		
X	1.00) REF	0.039 REF		

DETAIL AD



Please see www.freescale.com for the most current case outline.

Part 6 Design Considerations

6.1 Thermal Design Considerations

An estimation of the chip junction temperature, T_J, in °C can be obtained from the equation:

Equation 1: $T_J = T_A + (P_D \times R_{\theta JA})$

Where:

 T_A = ambient temperature °C

 $R_{\theta JA}$ = package junction-to-ambient thermal resistance °C/W

 P_D = power dissipation in package

Historically, thermal resistance has been expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

Equation 2:
$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

Where:

$$\begin{split} R_{\theta JA} &= \text{package junction-to-ambient thermal resistance }^\circ\text{C/W} \\ R_{\theta JC} &= \text{package junction-to-case thermal resistance }^\circ\text{C/W} \\ R_{\theta CA} &= \text{package case-to-ambient thermal resistance }^\circ\text{C/W} \end{split}$$

 $R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For example, the user can change the air flow around the device, add a heat sink, change the mounting arrangement on the Printed Circuit Board (PCB), or otherwise change the thermal dissipation capability of the area surrounding the device on the PCB. This model is most useful for ceramic packages with heat sinks; some 90% of the heat flow is dissipated through the case to the heat sink and out to the ambient environment. For ceramic packages, in situations where the heat flow is split between a path to the case and an alternate path through the PCB, analysis of the device thermal performance may need the additional modeling capability of a system level thermal simulation tool.

The thermal performance of plastic packages is more dependent on the temperature of the PCB to which the package is mounted. Again, if the estimations obtained from $R_{\theta JA}$ do not satisfactorily answer whether the thermal performance is adequate, a system level model may be appropriate.

A complicating factor is the existence of three common definitions for determining the junction-to-case thermal resistance in plastic packages:

- Measure the thermal resistance from the junction to the outside surface of the package (case) closest to the chip mounting area when that surface has a proper heat sink. This is done to minimize temperature variation across the surface.
- Measure the thermal resistance from the junction to where the leads are attached to the case. This definition is approximately equal to a junction to board thermal resistance.
- Use the value obtained by the equation $(T_J T_T)/P_D$ where T_T is the temperature of the package case determined by a thermocouple.

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As noted above, the junction-to-case thermal resistances quoted in this data sheet are determined using the first definition. From a practical standpoint, that value is also suitable for determining the junction temperature from a case thermocouple reading in forced convection environments. In natural convection, using the junction-to-case thermal resistance to estimate junction temperature from a thermocouple reading on the case of the package will estimate a junction temperature slightly hotter than actual. Hence, the new thermal metric, Thermal Characterization Parameter, or Ψ_{JT} , has been defined to be $(T_J - T_T)/P_D$. This value gives a better estimate of the junction temperature readings of packages are subject to significant errors caused by inadequate attachment of the sensor to the surface and to errors caused by heat loss to the sensor. The recommended technique is to attach a 40-gauge thermocouple wire and bead to the top center of the package with thermally conductive epoxy.

6.2 Electrical Design Considerations

CAUTION

This device contains protective circuitry to guard against damage due to high static voltage or electrical fields. However, normal precautions are advised to avoid application of any voltages higher than maximum rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate voltage level.

Use the following list of considerations to assure correct operation:

- Provide a low-impedance path from the board power supply to each V_{DD} pin on the controller, and from the board ground to each V_{SS} (GND) pin.
- The minimum bypass requirement is to place six 0.01–0.1 μ F capacitors positioned as close as possible to the package supply pins. The recommended bypass configuration is to place one bypass capacitor on each of the ten V_{DD}/V_{SS} pairs, including V_{DDA}/V_{SSA}.
- Ensure that capacitor leads and associated printed circuit traces that connect to the chip V_{DD} and V_{SS} (GND) pins are less than 0.5 inch per capacitor lead.
- Use at least a four-layer Printed Circuit Board (PCB) with two inner layers for V_{DD} and GND.
- Bypass the V_{DD} and GND layers of the PCB with approximately 100 μ F, preferably with a high-grade capacitor such as a tantalum capacitor.
- Because the device's output signals have fast rise and fall times, PCB trace lengths should be minimal.

- Consider all device loads as well as parasitic capacitance due to PCB traces when calculating capacitance. This is especially critical in systems with higher capacitive loads that could create higher transient currents in the V_{DD} and GND circuits.
- All inputs must be terminated (i.e., not allowed to float) using CMOS levels.
- Take special care to minimize noise levels on the V_{DDA} and V_{SSA} pins.
- When using Wired-OR mode on the SPI or the IRQx pins, the user must provide an external pull-up device.
- Designs that utilize the TRST pin for JTAG port or Enhance OnCE module functionality (such as development or debugging systems) should allow a means to assert TRST whenever RESET is asserted, as well as a means to assert TRST independently of RESET. Designs that do not require debugging functionality, such as consumer products, should tie these pins together.
- The internal <u>POR</u> (Power on Reset) will reset the part at power on with reset asserted or pulled high but requires that <u>TRST</u> be asserted at power on.

Part 7 Ordering Information

Table 7-1 lists the pertinent information needed to place an order. Consult a Freescale Semiconductor sales office or authorized distributor to determine availability and to order parts.

Part	Supply Voltage	Package Type	Pin Count	Frequency (MHz)	Order Number
DSP56855	1.8V, 3.3V	Low-Profile Quad Flat Pack (LQFP)	100	120	DSP56855BU120
DSP56855	1.8V, 3.3V	Low-Profile Quad Flat Pack (LQFP)	100	120	DSP56855BUE *

Table 7-1 56855 Ordering Information

*This package is RoHS compliant.

Electrical Design Considerations

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